3DD60

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion,low resistance liner process.Heavy out-put Current,small saturation voltage drop. Excellent out-put characteristic.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify,power adjustment,DC conversion.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150	
Emitter-Base Voltage	V_{EBO}	V	3					
Max. Collector Current	I_{CM}	A	2.5					
Max. Collector Dissipation	P_{CM}	W	25					Tc:75°C
Junction Temperature	T_{jm}	°C	175					
Storage Temperature	T_{stg}	°C	-55~+175					
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.5					V_{CE}=20V
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.2					I_C=1.25A,I_B=0.25A
DC Current Gain	h_{FE}		Min.:10					V_{CE}=5V,I_C=1.25A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	I_C=5mA
			30	50	80	110	150	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	3					I_E=10mA

h_{FE} Colored:

Color	Brown	Red	Orange
h_{FE}	10~20	20~30	30~

Outline and Dimensions: